

FIG. 1A

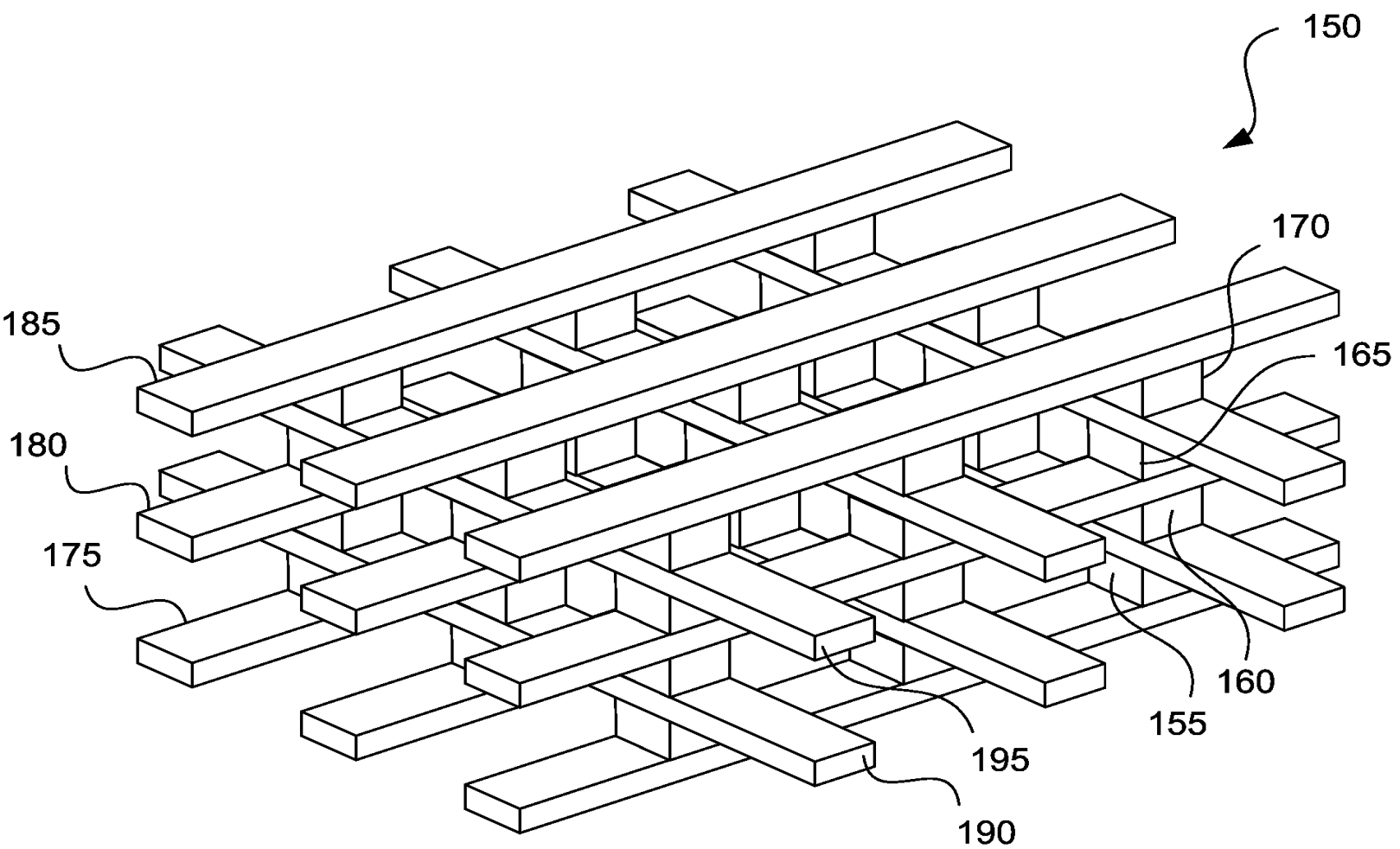


FIG. 1B

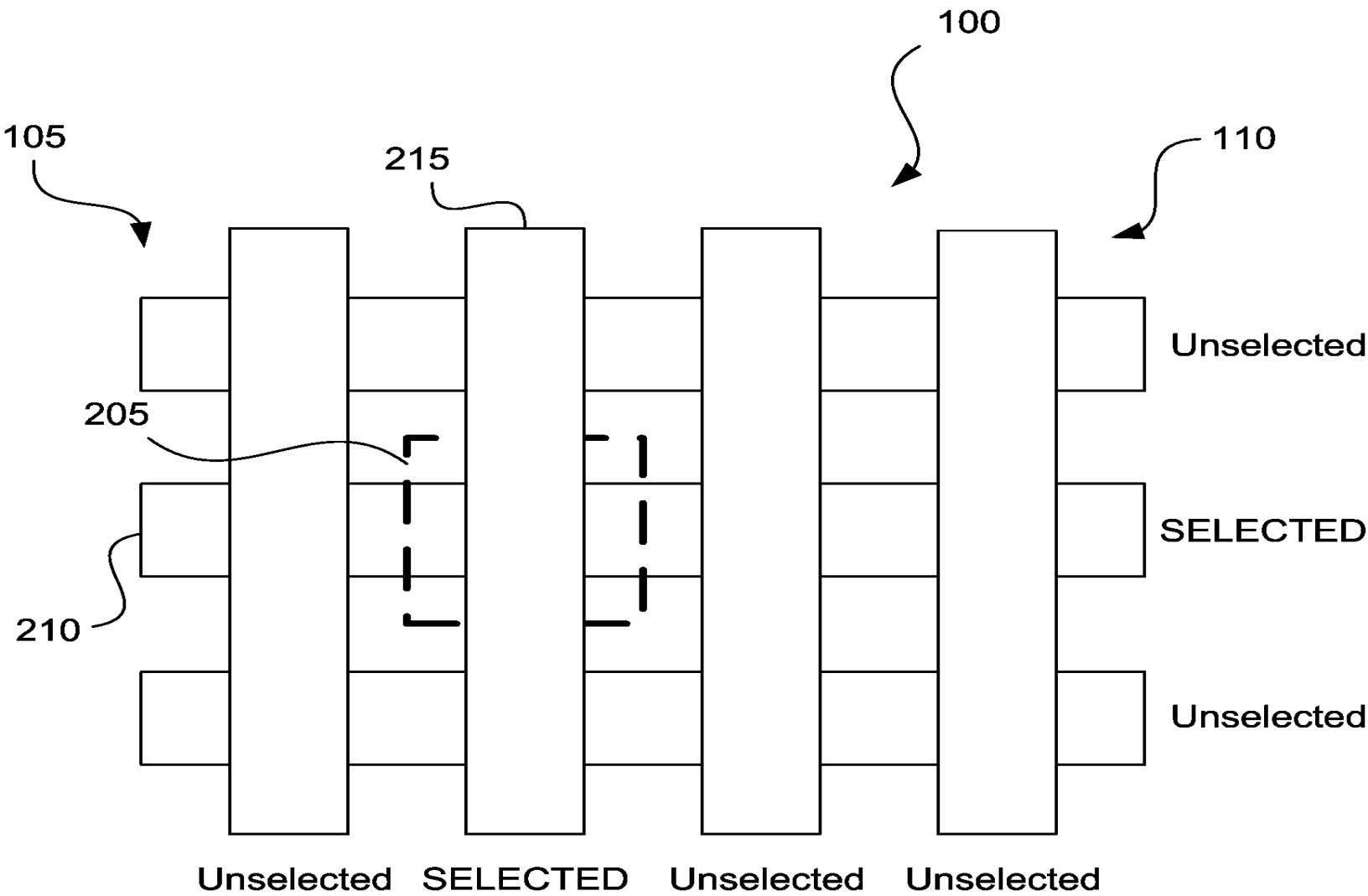


FIG. 2A

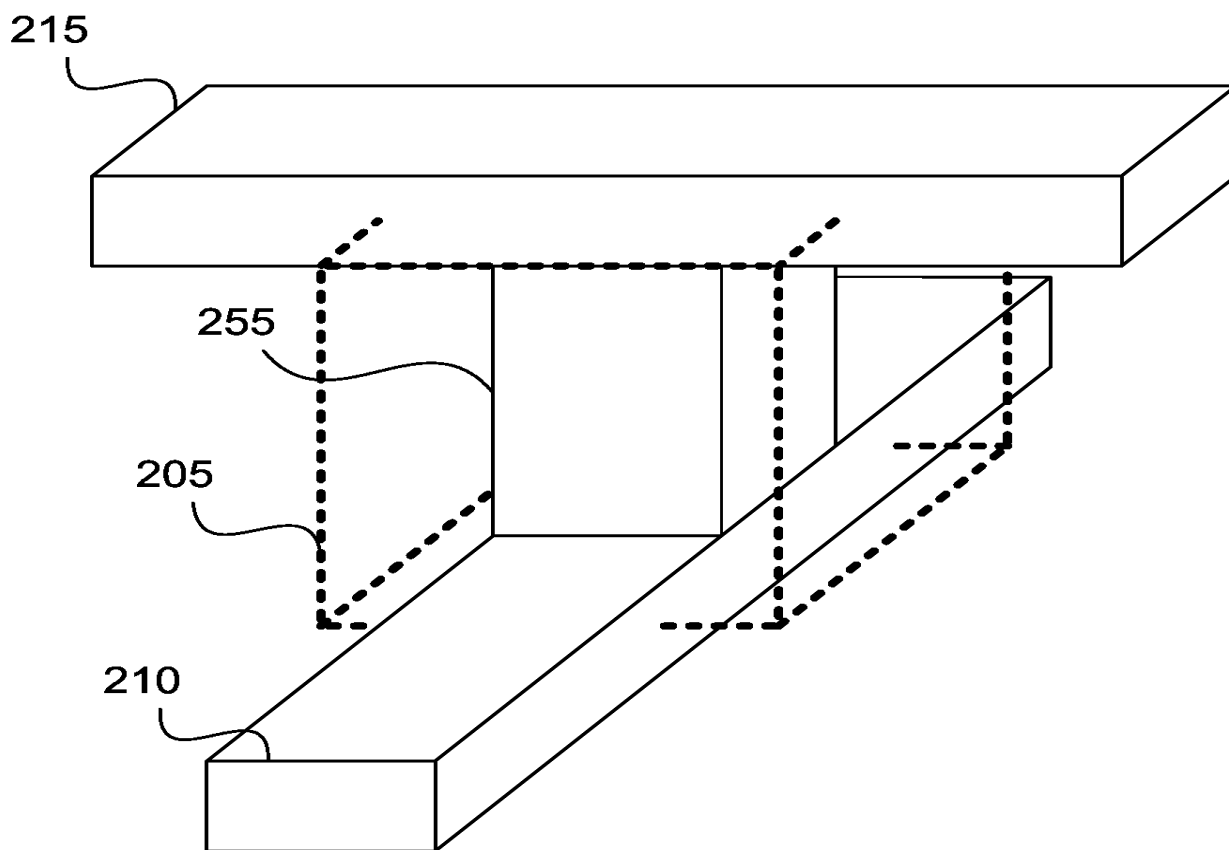


FIG. 2B

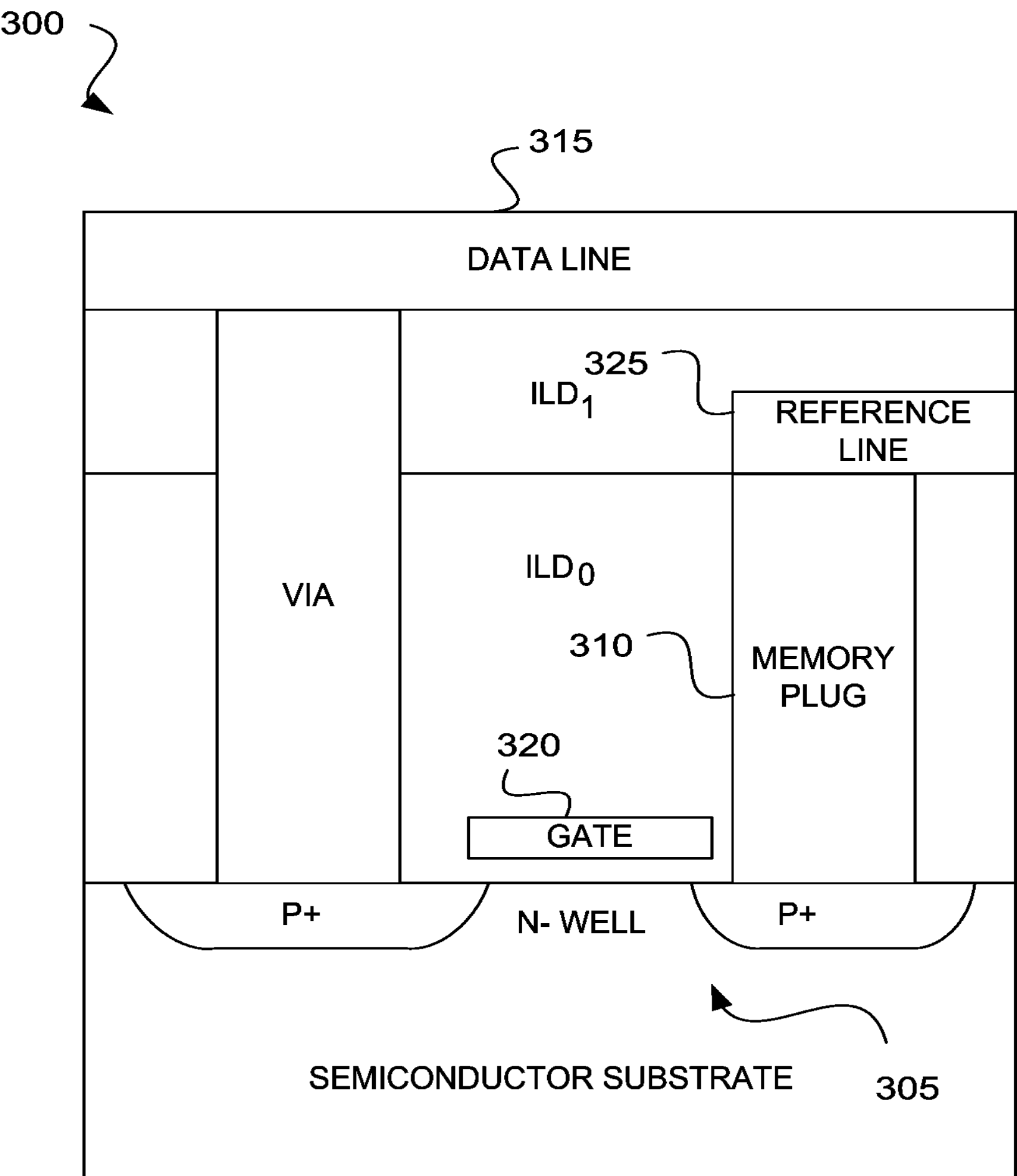


FIG. 3

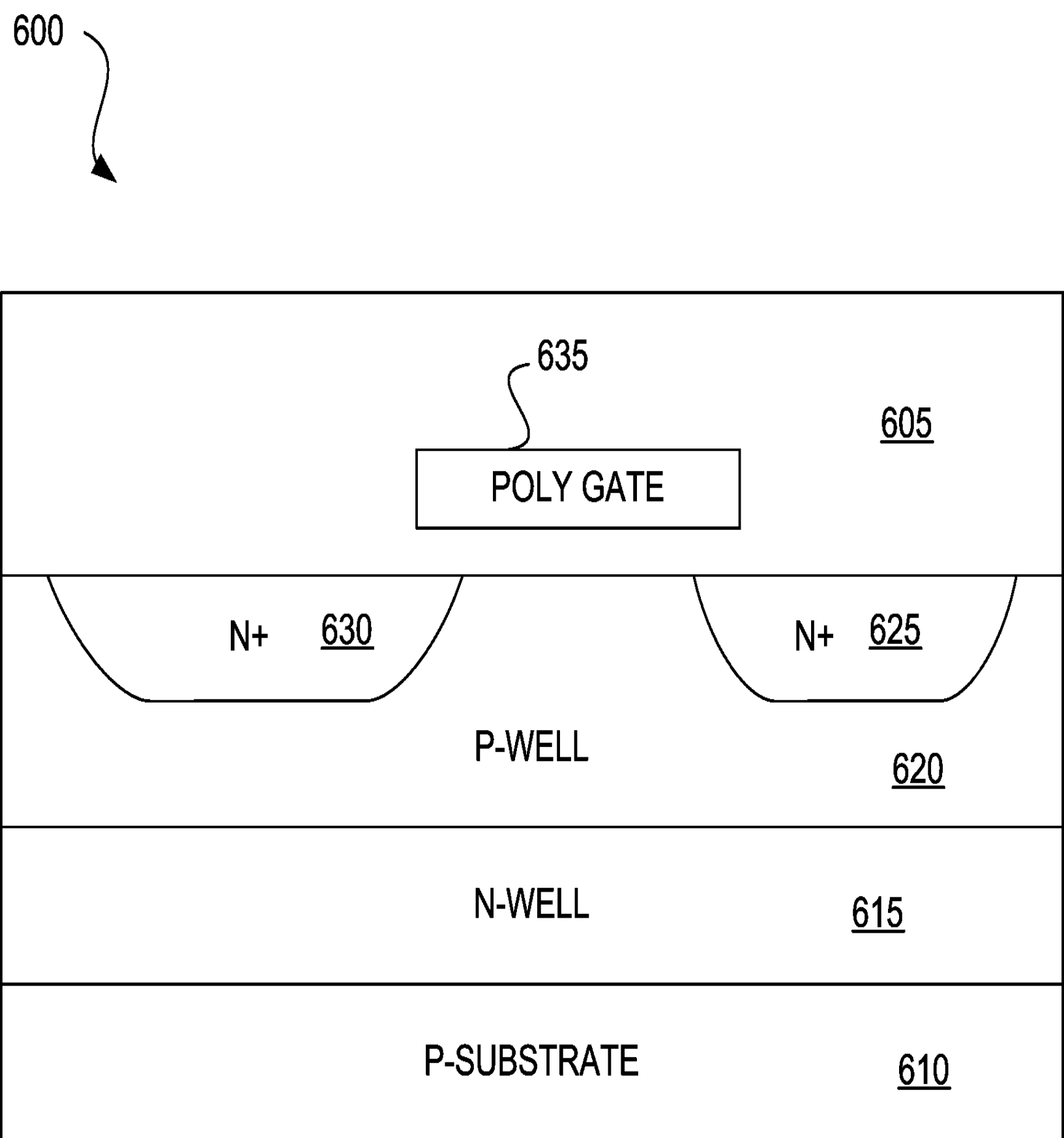


FIG. 4

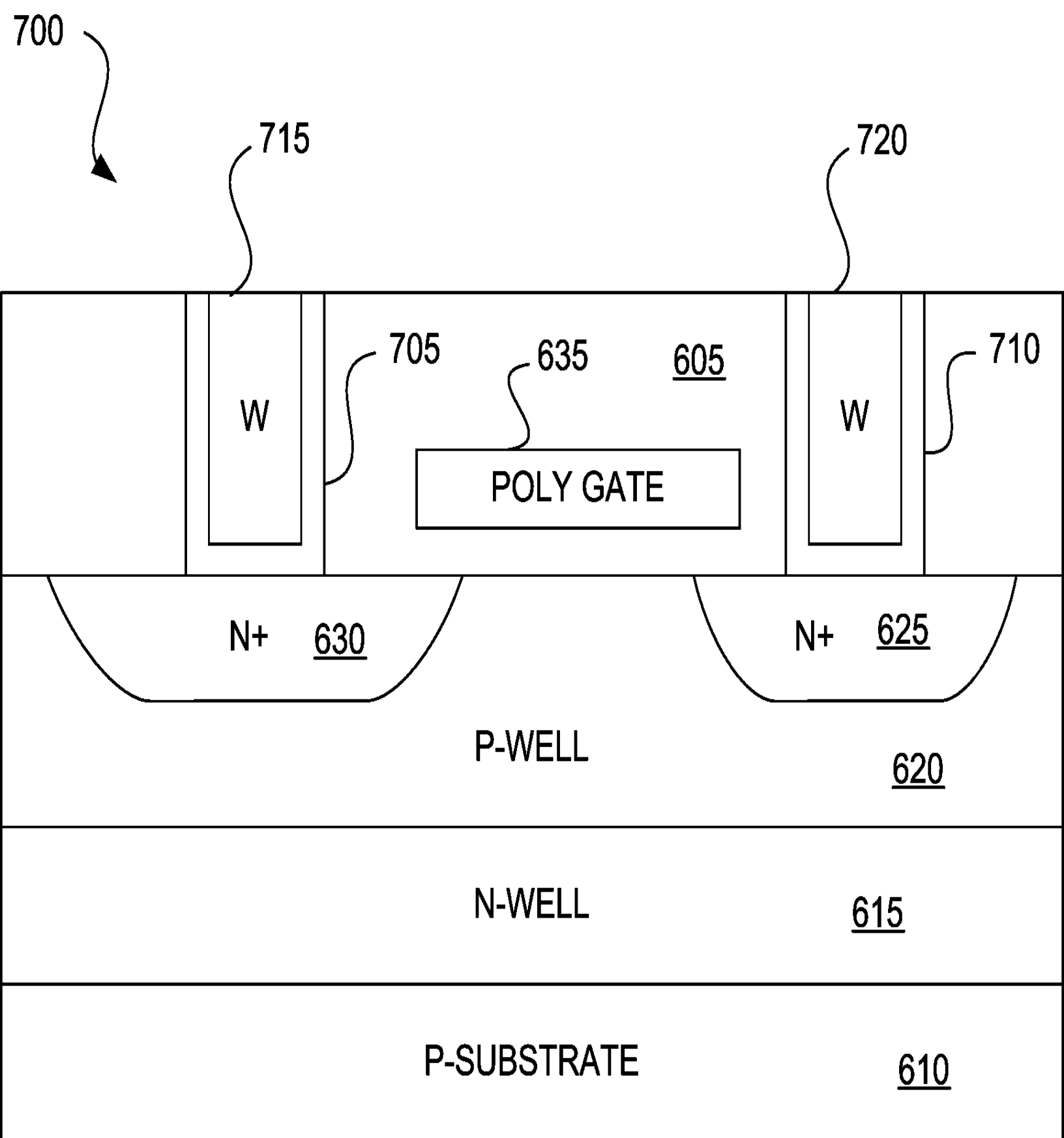


FIG. 5

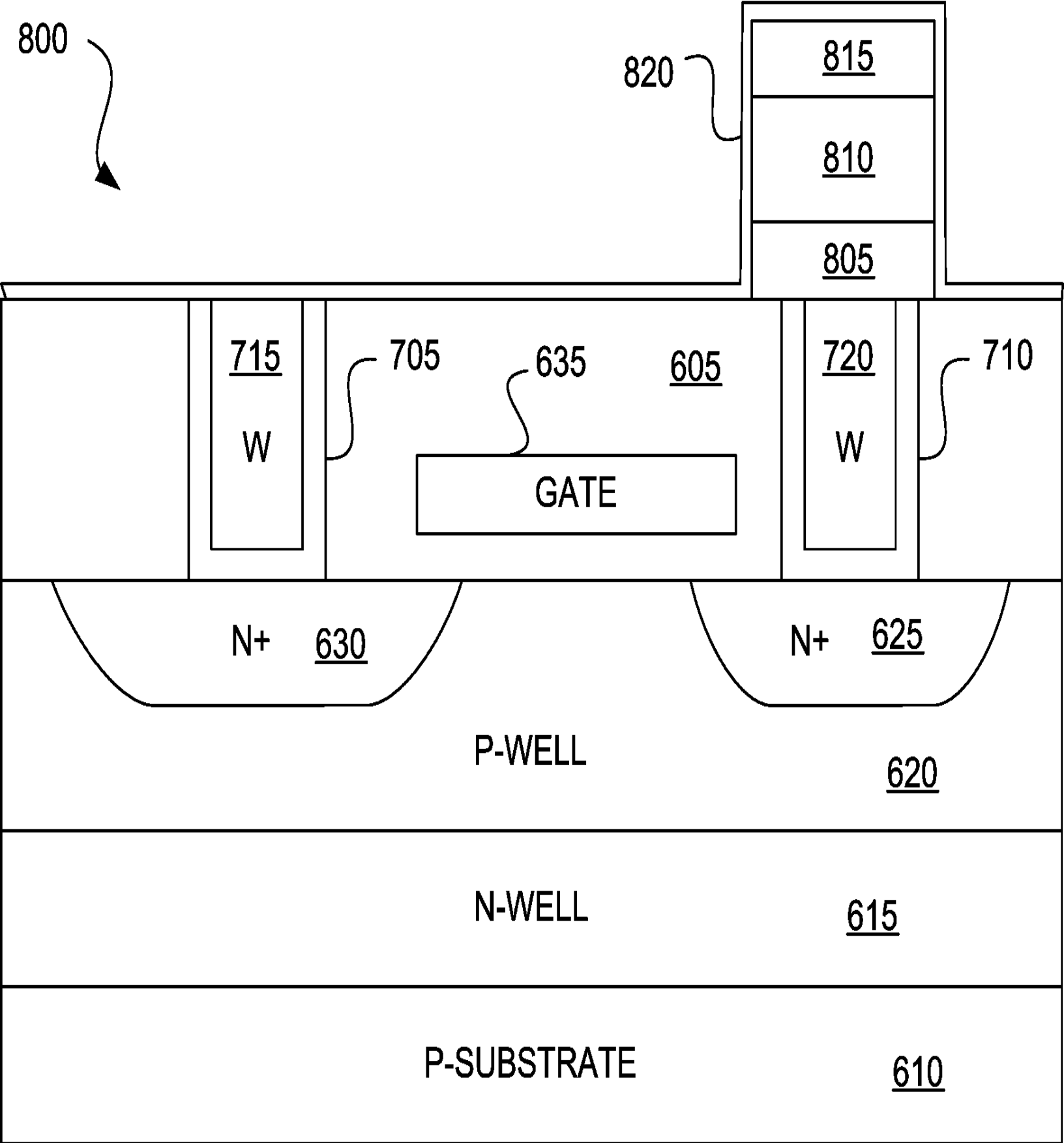


FIG. 6

900

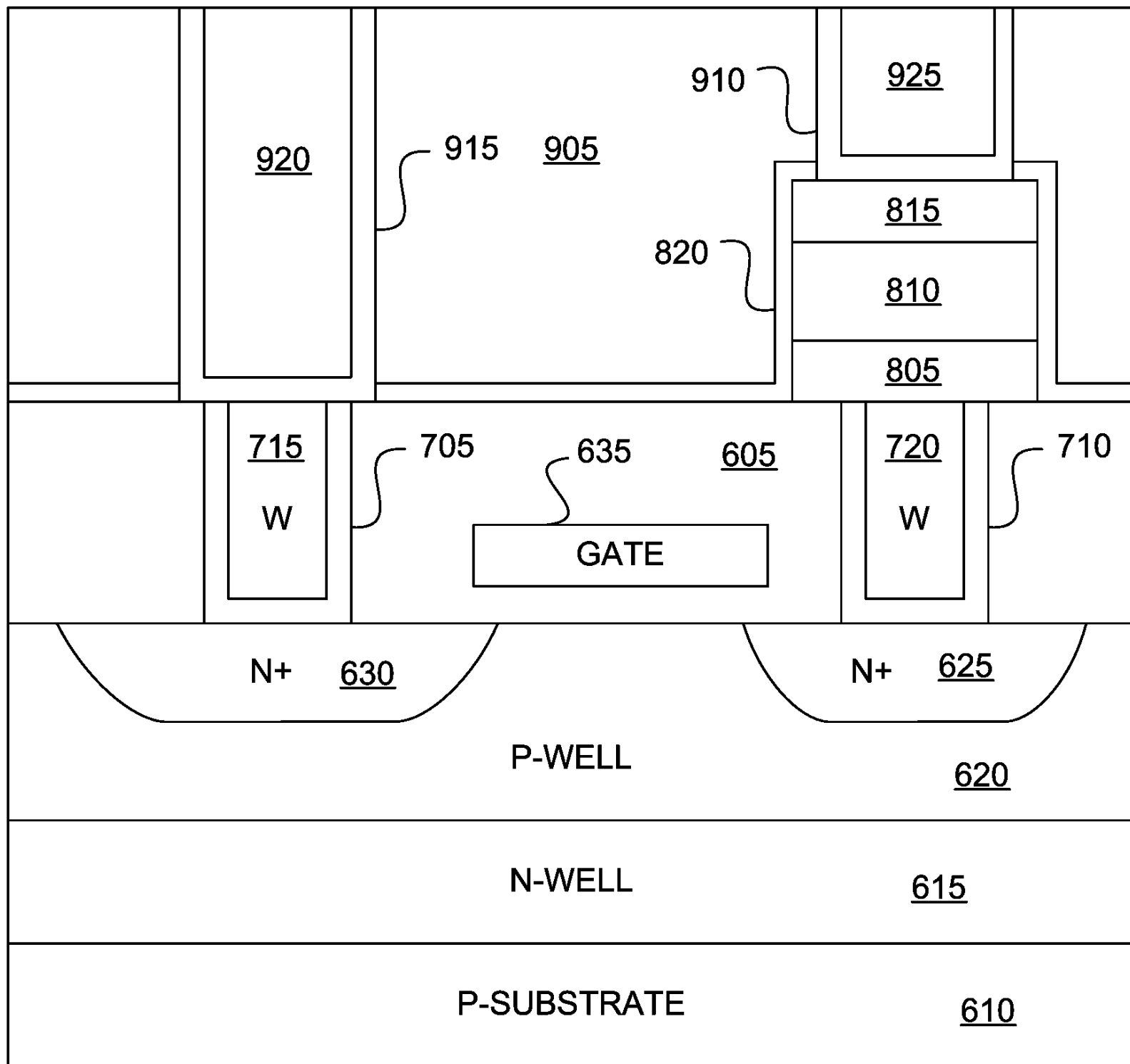


FIG. 7

This diagram illustrates a cross-sectional view of a semiconductor device. The structure is built on a **P-SUBSTRATE** (610). Above the substrate is an **N-WELL** (615). Within the N-well, there are two **N+** regions (630 and 625) and a **P-WELL** region. A **GATE** structure (635) is positioned over the P-well. The device includes several layers and components: **1020** (top layer), **1025** (layer below 1020), **1010** (layer below 1025), **1015** (layer below 1010), **920** (layer below 1015), **905** (layer below 920), **910** (layer below 905), **915** (layer below 910), **925** (layer below 915), **815** (layer below 925), **810** (layer below 815), **805** (layer below 810), **715** (layer below 805), **720** (layer below 715), **710** (layer below 720), **705** (layer below 710), **605** (layer below 705), **630** (N+ region), **625** (N+ region), **620** (P-well region), **615** (N-well region), and **610** (P-substrate). The diagram also shows a **W** (well) region and a **GATE** structure.

FIG. 8

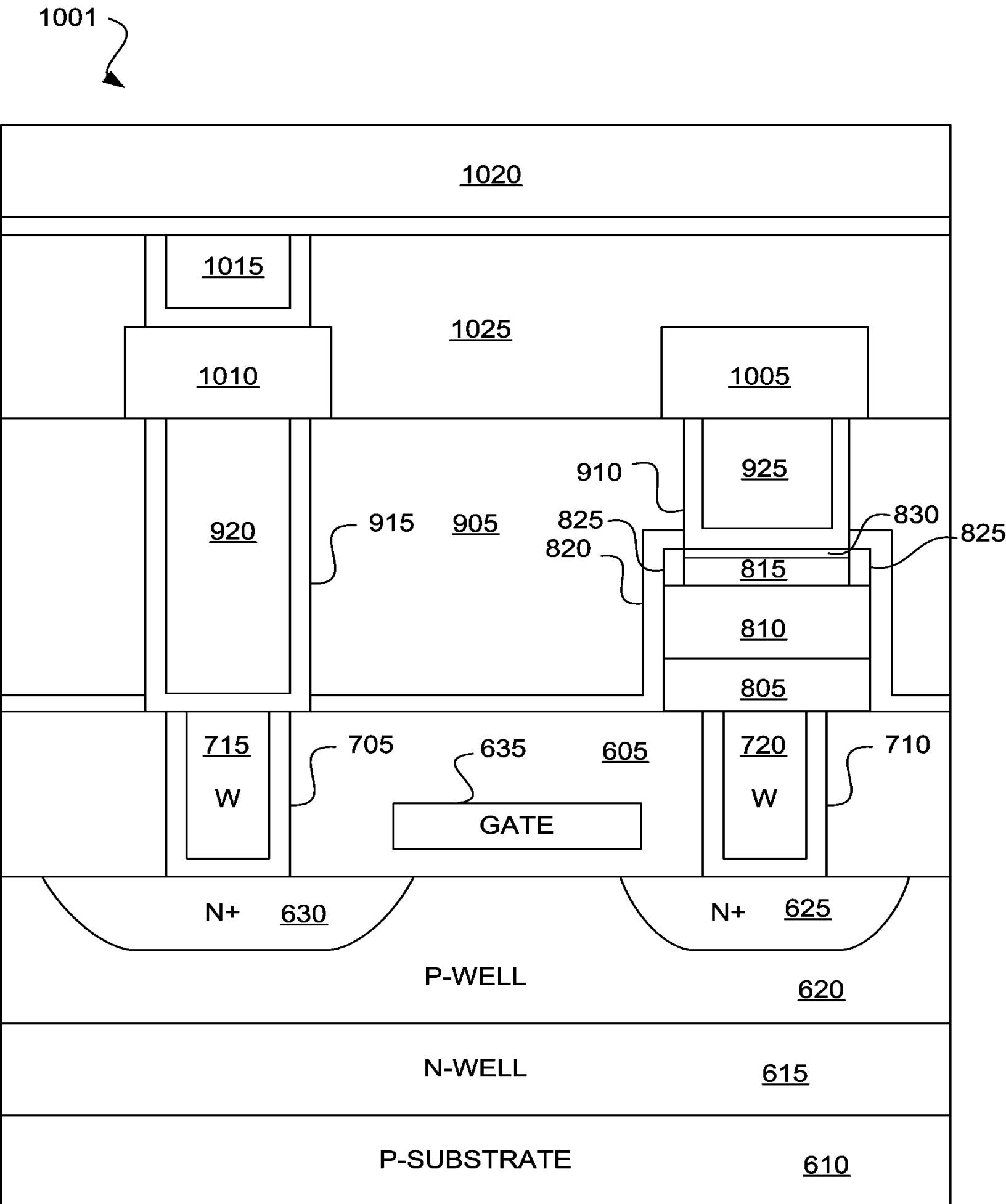


FIG. 9

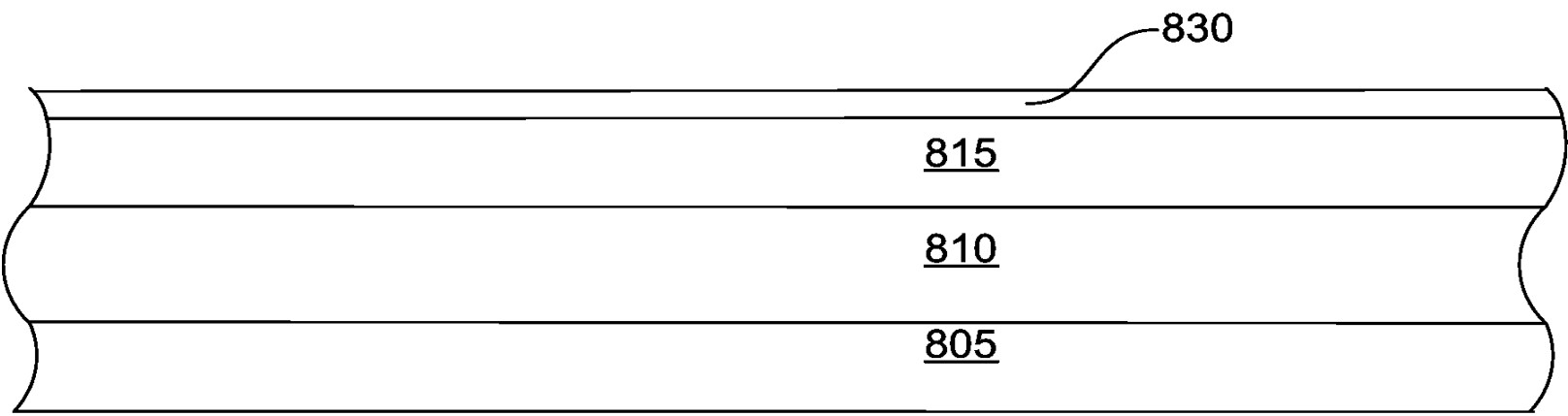


FIG. 10A

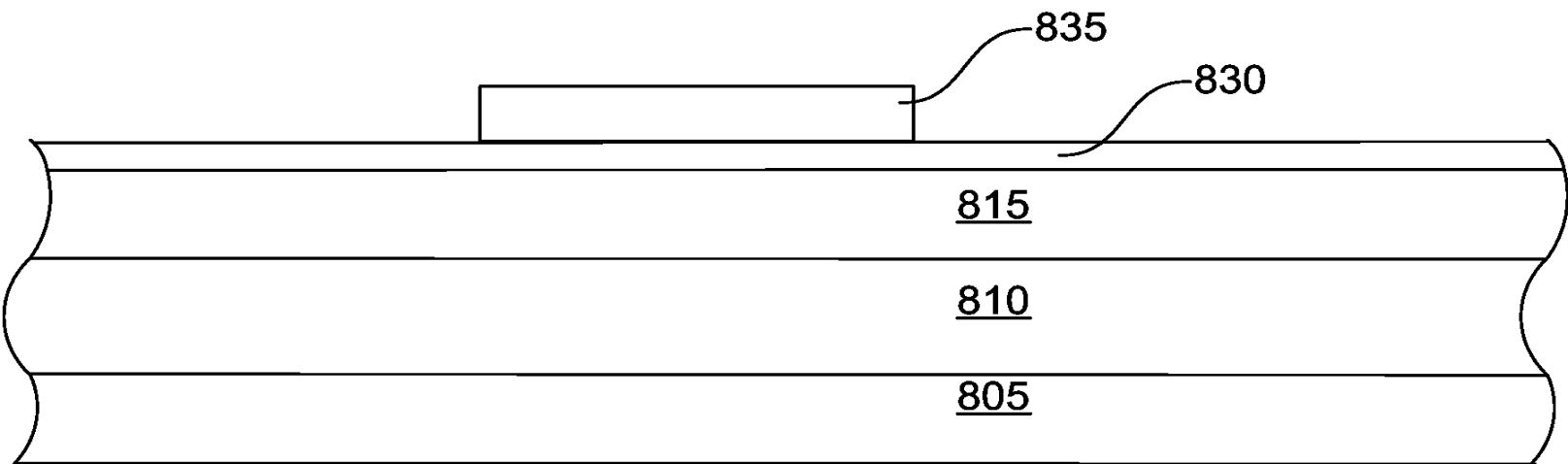


FIG. 10B

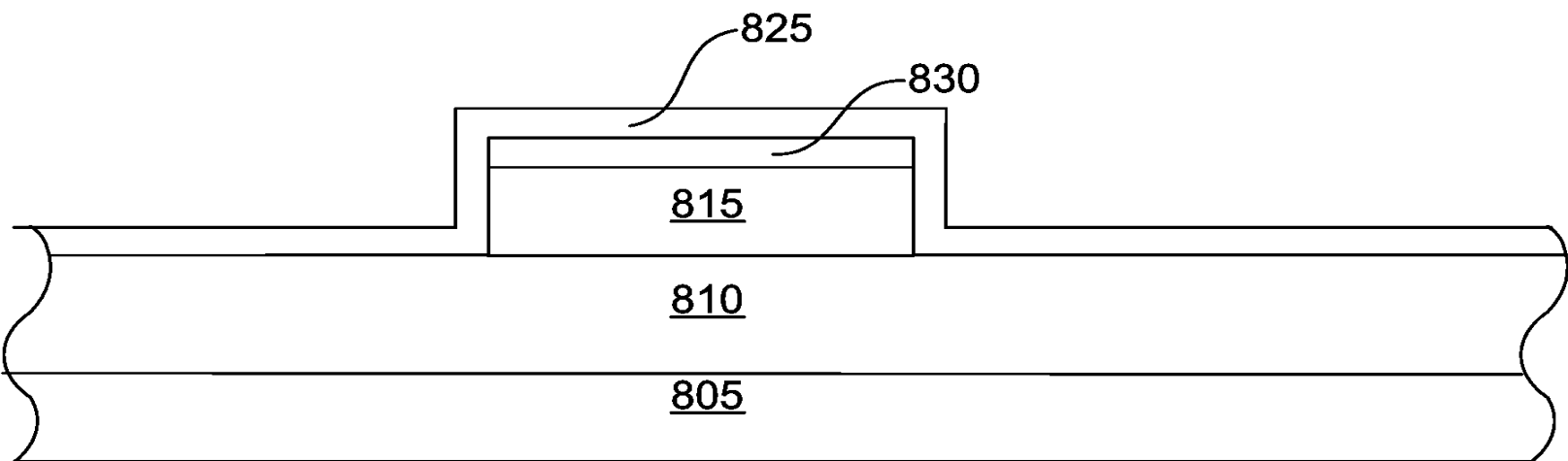


FIG. 10C

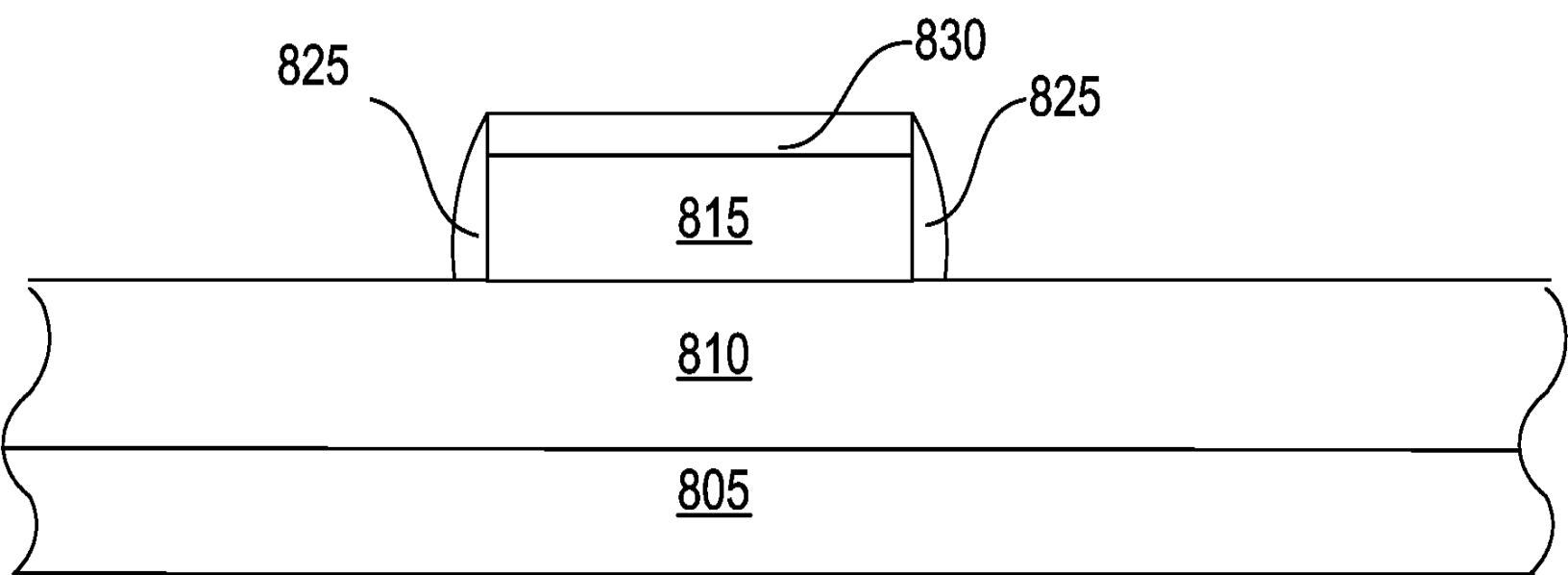


FIG. 10D

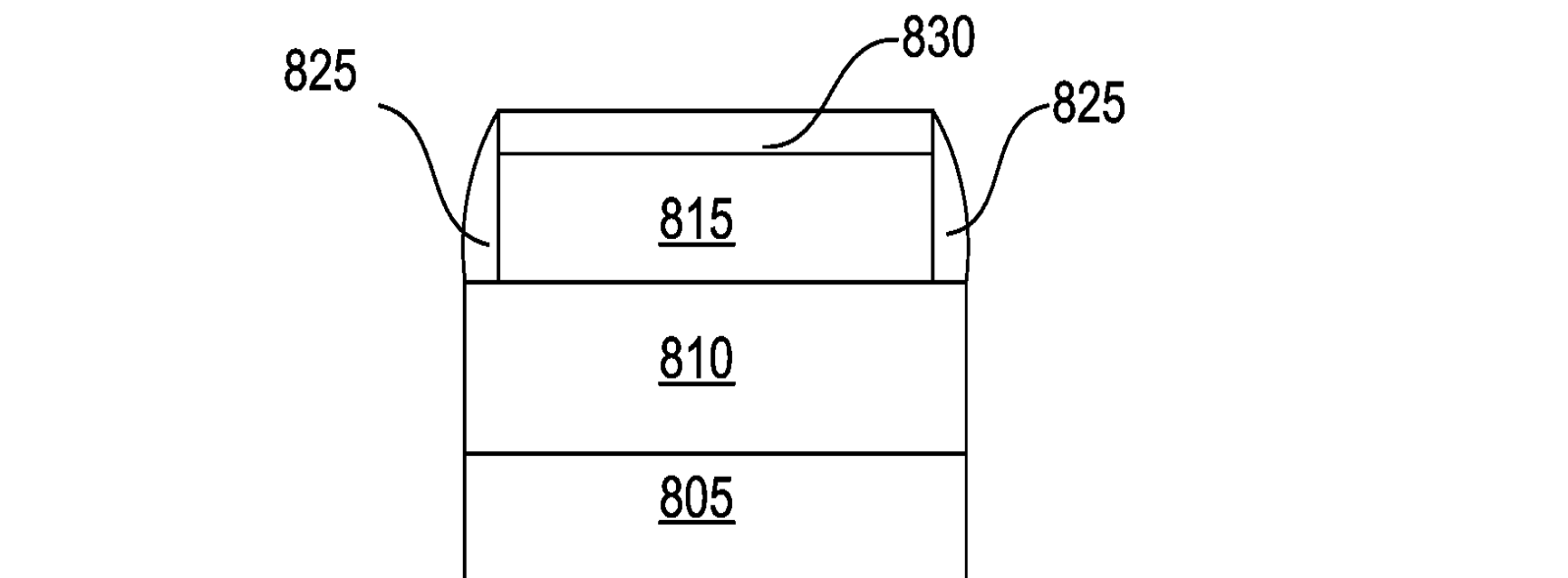


FIG. 10E

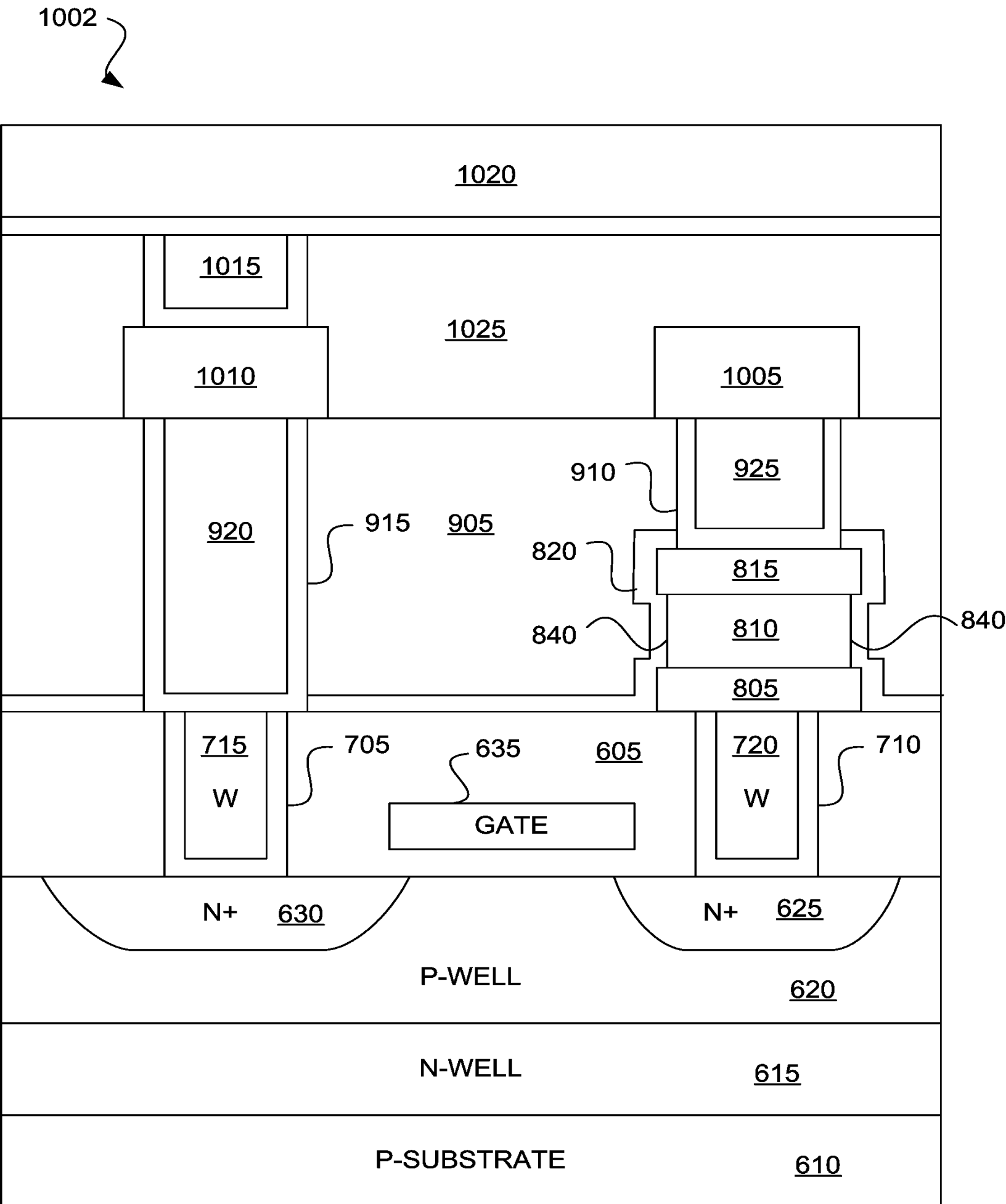


FIG. 11